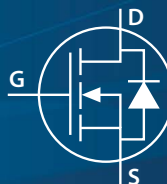
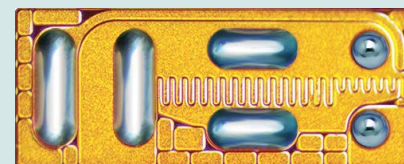


EPC8002 – Enhancement Mode Power Transistor

 $V_{DS}, 65\text{ V}$
 $R_{DS(on)}, 480\text{ m}\Omega$
 $I_D, 2\text{ A}$


Halogen-Free

Gallium Nitride is grown on Silicon Wafers and processed using standard CMOS equipment leveraging the infrastructure that has been developed over the last 55 years. GaN's exceptionally high electron mobility and low temperature coefficient allows very low $R_{DS(on)}$, while its lateral device structure and majority carrier diode provide exceptionally low Q_G and zero Q_{RR} . The end result is a device that can handle tasks where very high switching frequency, and low on-time are beneficial as well as those where on-state losses dominate.



EPC8002 eGaN FETs are supplied only in passivated die form with solder bars
Die Size: 2.1 mm x 0.85 mm

Applications

- Ultra High Speed DC-DC Conversion
- RF Envelope Tracking
- Wireless Power Transfer
- Game Console and Industrial Movement Sensing (LiDAR)

Benefits

- Ultra High Efficiency
- Ultra Low $R_{DS(on)}$
- Ultra Low Q_G
- Ultra Small Footprint

www.epc-co.com/epc/Products/eGaNfets/EPC8002.aspx

Maximum Ratings			
PARAMETER		VALUE	UNIT
V_{DS}	Drain-to-Source Voltage (Continuous)	65	V
	Drain-to-Source Voltage (up to 10,000 5 ms pulses at 150°C)	78	
I_D	Continuous ($T_A = 25^\circ\text{C}$, $R_{\theta JA} = 36^\circ\text{C/W}$)	2	A
	Pulsed (25°C , $T_{PULSE} = 300\text{ }\mu\text{s}$)	2	
V_{GS}	Gate-to-Source Voltage	6	V
	Gate-to-Source Voltage	-4	
T_J	Operating Temperature	-40 to 150	$^\circ\text{C}$
T_{STG}	Storage Temperature	-40 to 150	

Static Characteristics ($T_J = 25^\circ\text{C}$ unless otherwise stated)						
PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
BV_{DSS}	Drain-to-Source Voltage	$V_{GS} = 0\text{ V}$, $I_D = 125\text{ }\mu\text{A}$	65			V
I_{DSS}	Drain-Source Leakage	$V_{DS} = 52\text{ V}$, $V_{GS} = 0\text{ V}$		20	100	μA
I_{GSS}	Gate-to-Source Forward Leakage	$V_{GS} = 5\text{ V}$		0.1	1	mA
	Gate-to-Source Reverse Leakage	$V_{GS} = -4\text{ V}$		20	100	μA
$V_{GS(TH)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$, $I_D = 0.1\text{ mA}$	0.8	1.4	2.5	V
$R_{DS(on)}$	Drain-Source On Resistance	$V_{GS} = 5\text{ V}$, $I_D = 0.5\text{ A}$		380	480	$\text{m}\Omega$
V_{SD}	Source-Drain Forward Voltage	$I_S = 0.4\text{ A}$, $V_{GS} = 0\text{ V}$		2.6		V

Specifications are with substrate shorted to source where applicable.

Thermal Characteristics			
PARAMETER		TYP	UNIT
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	8.2	$^\circ\text{C/W}$
$R_{\theta JB}$	Thermal Resistance, Junction-to-Board	16	
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 1)	82	

Note 1: $R_{\theta JA}$ is determined with the device mounted on one square inch of copper pad, single layer 2 oz copper on FR4 board.

See http://epc-co.com/epc/documents/product-training/Appnote_Thermal_Performance_of_eGaN_FETs.pdf for details

Dynamic Characteristics ($T_J = 25^\circ\text{C}$ unless otherwise stated)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
C_{ISS}	Input Capacitance	$V_{DS} = 32.5\text{ V}, V_{GS} = 0\text{ V}$		20	24	pF
C_{RSS}	Reverse Transfer Capacitance			0.12	0.18	
C_{OSS}	Output Capacitance			6.7	10	
$C_{OSS(ER)}$	Effective Output Capacitance, Energy Related (Note 2)	$V_{DS} = 0\text{ to }32.5\text{ V}, V_{GS} = 0\text{ V}$		8.9		
$C_{OSS(TR)}$	Effective Output Capacitance, Time Related (Note 3)			10		
R_G	Gate Resistance			0.3		Ω
Q_G	Total Gate Charge	$V_{DS} = 32.5\text{ V}, V_{GS} = 5\text{ V}, I_D = 0.5\text{ A}$		133	167	pC
Q_{GS}	Gate-to-Source Charge	$V_{DS} = 32.5\text{ V}, I_D = 0.5\text{ A}$		57		
Q_{GD}	Gate-to-Drain Charge			15	26	
$Q_{G(TH)}$	Gate Charge at Threshold			46		
Q_{OSS}	Output Charge	$V_{DS} = 32.5\text{ V}, V_{GS} = 0\text{ V}$		334	500	
Q_{RR}	Source-Drain Recovery Charge			0		

Note 2: $C_{OSS(ER)}$ is a fixed capacitance that gives the same stored energy as C_{OSS} while V_{DS} is rising from 0 to 50% BVDSS.

Note 3: $C_{OSS(TR)}$ is a fixed capacitance that gives the same charging time as C_{OSS} while V_{DS} is rising from 0 to 50% BVDSS.

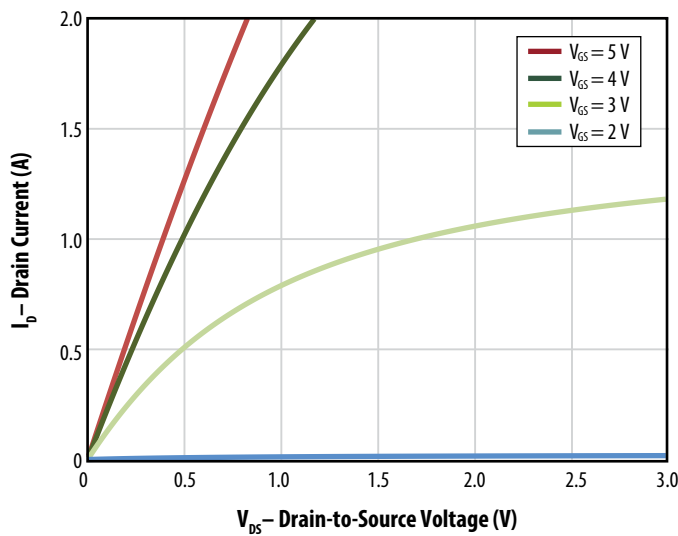
Figure 1: Typical Output Characteristics at 25°C 

Figure 2: Transfer Characteristics

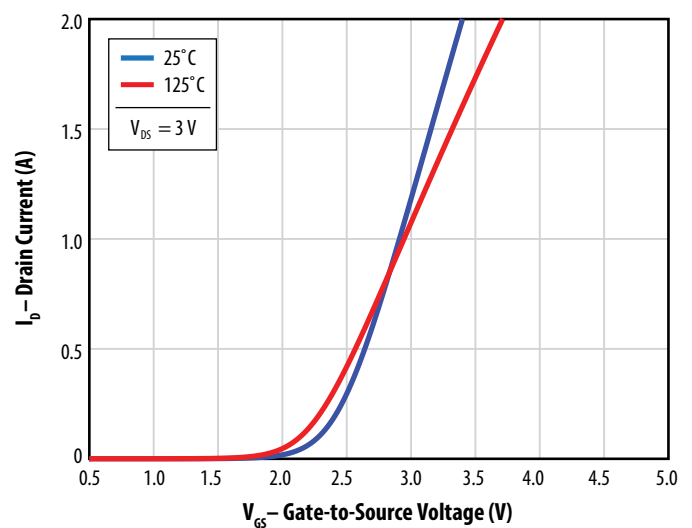
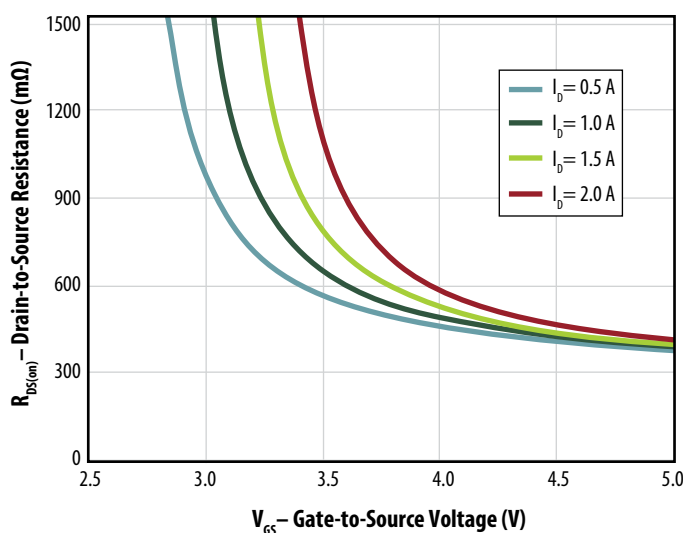
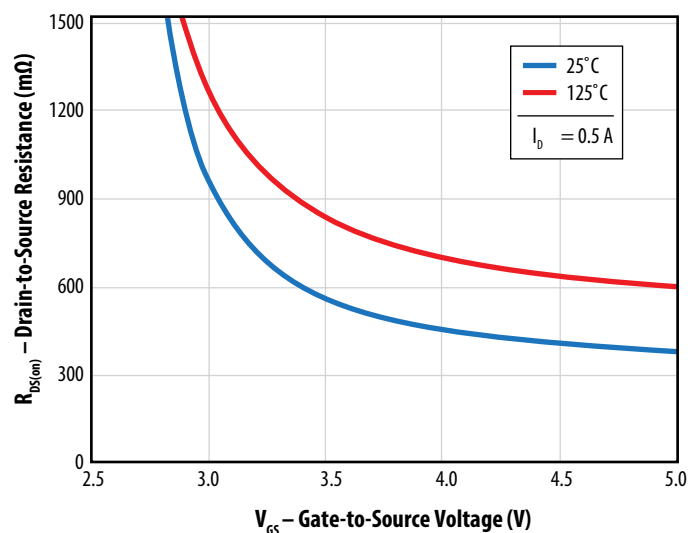
Figure 3: $R_{DS(on)}$ vs V_{GS} for Various Drain CurrentsFigure 4: $R_{DS(on)}$ vs V_{GS} for Various Temperatures

Figure 5: Capacitance (Linear Scale)

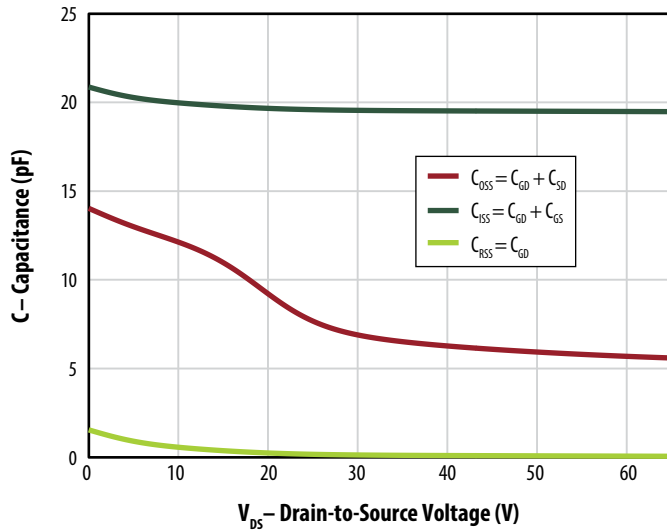


Figure 5A: Capacitance (Log Scale)

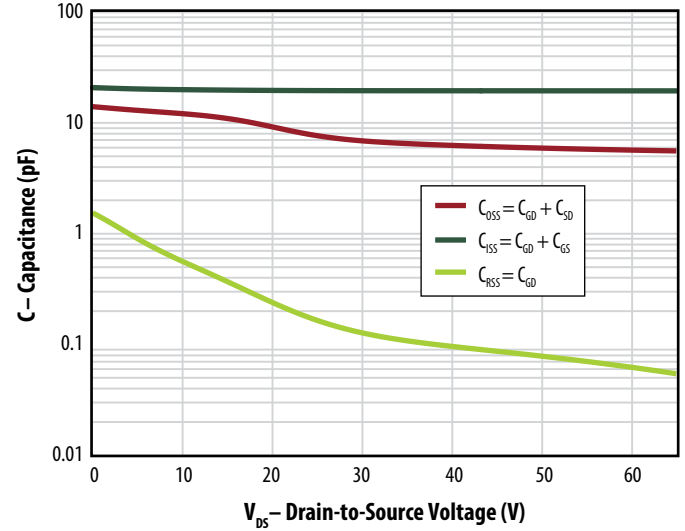


Figure 6: Gate Charge

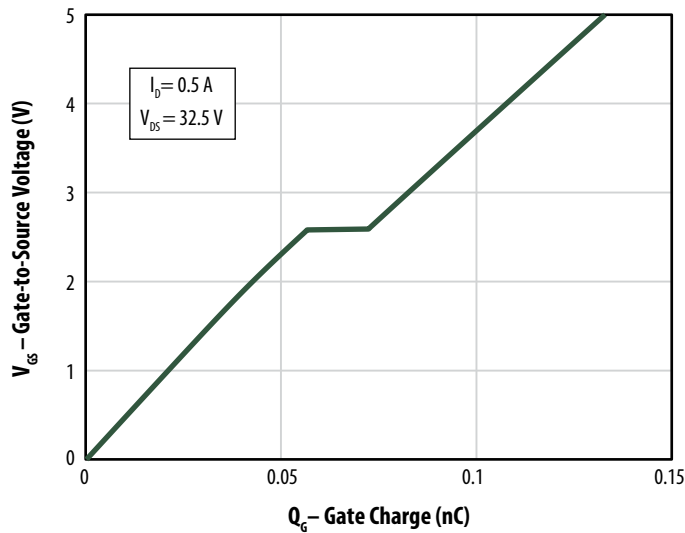


Figure 7: Reverse Drain-Source Characteristics

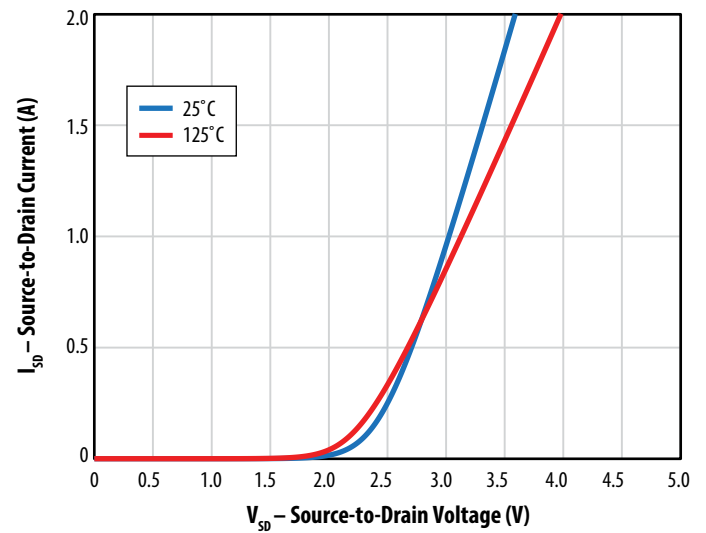


Figure 8: Normalized On-State Resistance vs Temperature

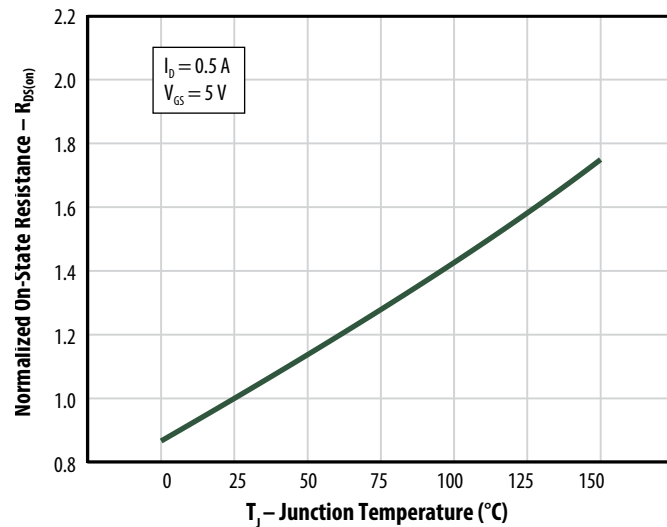


Figure 9: Normalized Threshold Voltage vs Temperature

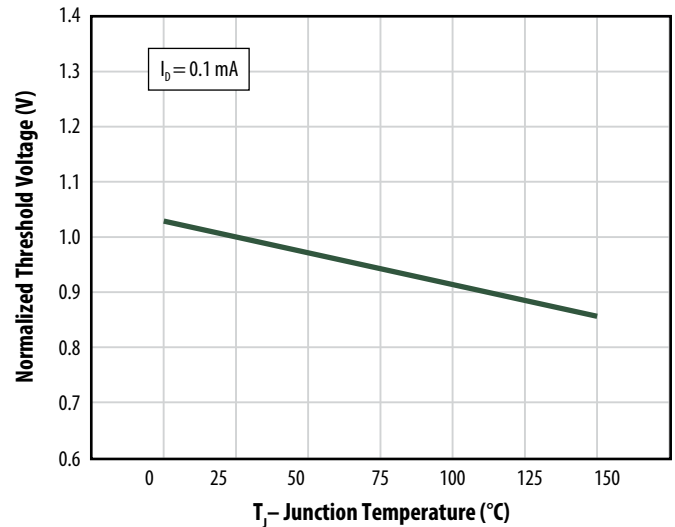
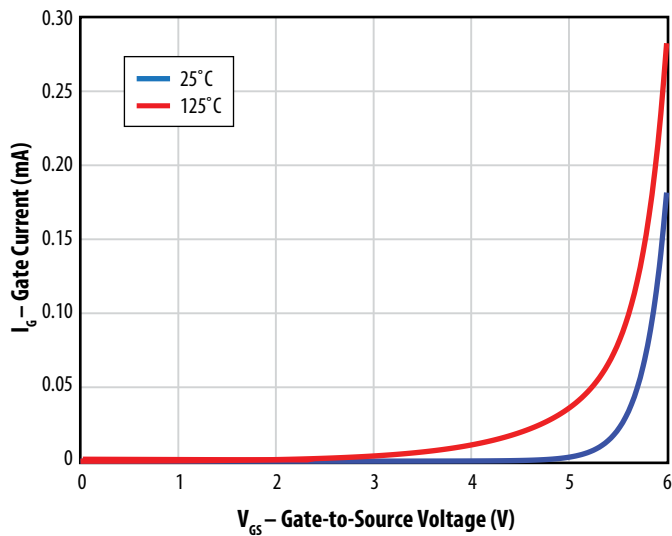
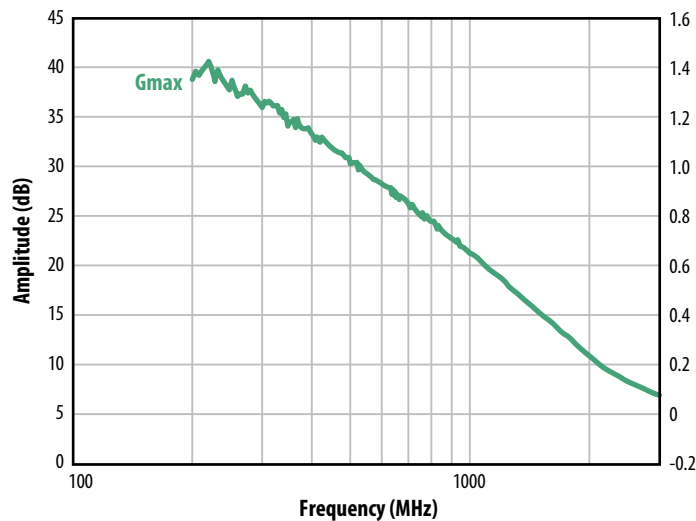


Figure 10: Gate Leakage Current



All measurements were done with substrate shorted to source.

Figure 12: Gain Chart



Frequency [MHz]	Gate (Z_{GS}) [Ω]	Drain (Z_{DS}) [Ω]
200	3.09 - j29.97	63.13 - j71.32
500	2.20 - j11.92	15.96 - j46.65
1000	1.14 - j4.46	3.35 - j23.47
1200	0.95 - j2.76	1.91 - j18.52
1500	0.87 - j0.55	1.66 - j12.66
2000	1.09 + j2.61	2.28 - j6.12
2400	1.44 + j4.87	4.35 - j2.80
3000	2.36 + j8.79	6.41 + j0.69

S-Parameter Table - Download S-parameter files at www.epc-co.com

Figure 11: Smith Chart

S-Parameter Characteristics
 $V_{GSQ} = 1.17$ V, $V_{DSQ} = 30$ V, $I_{DQ} = 0.2$ A
 Pulsed Measurement, Heat-Sink Installed, $Z_0 = 50 \Omega$

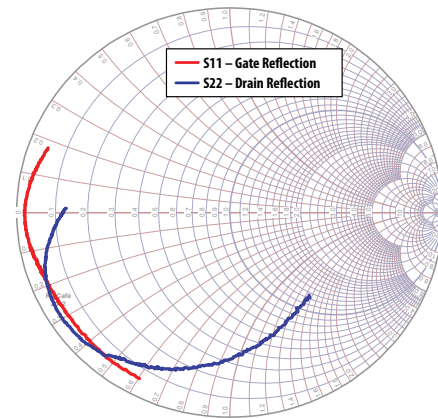


Figure 13: Device Reflection

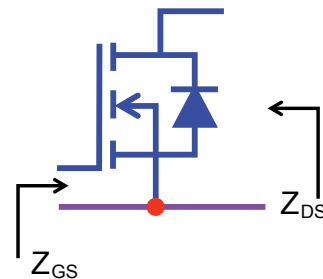


Figure 14: Taper and Reference Plane details – Device Connection

Micro-Strip design: 2-layer
 ½ oz (17.5 μ m) thick copper
 30 mil thick R04350 substrate

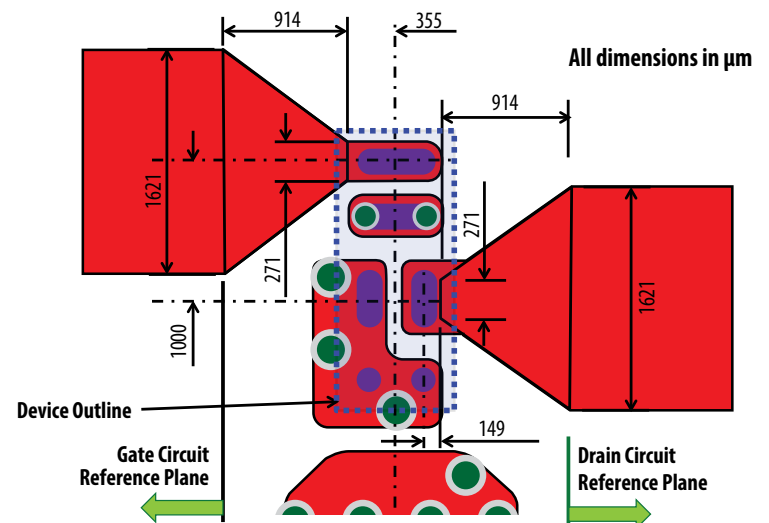


Figure 15: Transient Thermal Response Curves

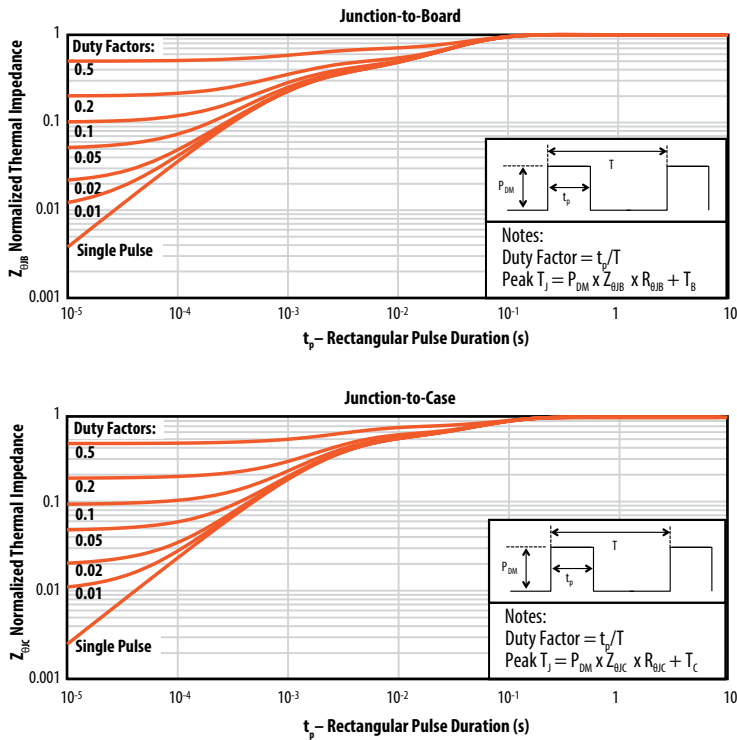
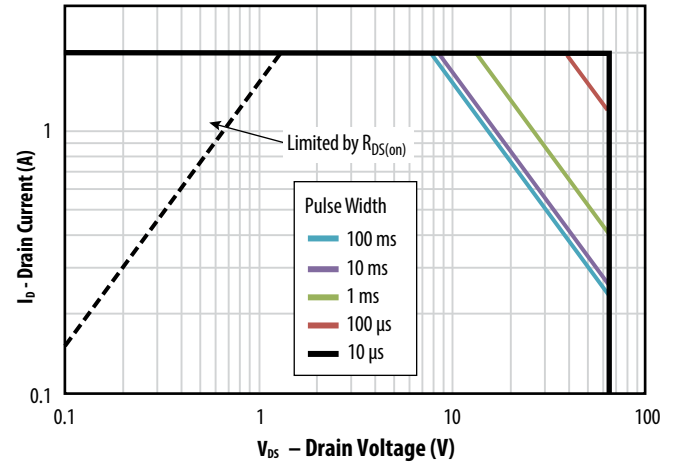
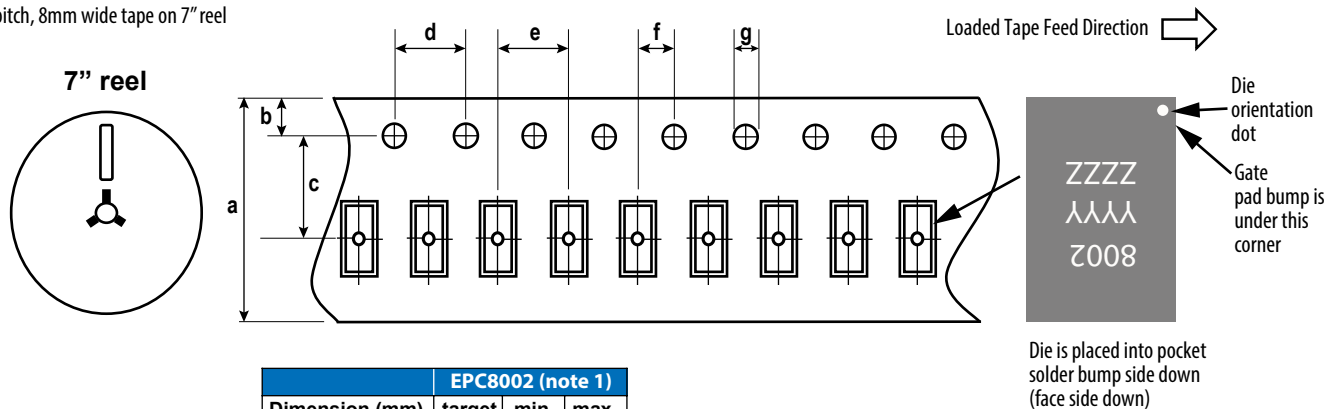


Figure 16: Safe Operating Area



TAPE AND REEL CONFIGURATION

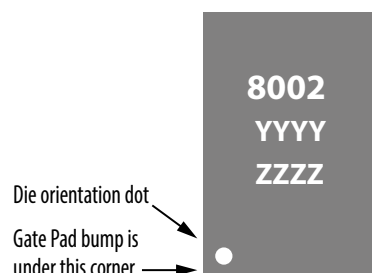
4mm pitch, 8mm wide tape on 7" reel



EPC8002 (note 1)			
Dimension (mm)	target	min	max
a	8.00	7.90	8.30
b	1.75	1.65	1.85
c (see note)	3.50	3.45	3.55
d	4.00	3.90	4.10
e	4.00	3.90	4.10
f (see note)	2.00	1.95	2.05
g	1.5	1.5	1.6

Note 1: MSL 1 (moisture sensitivity level 1) classified according to IPC/JEDEC industry standard.
Note 2: Pocket position is relative to the sprocket hole measured as true position of the pocket, not the pocket hole.

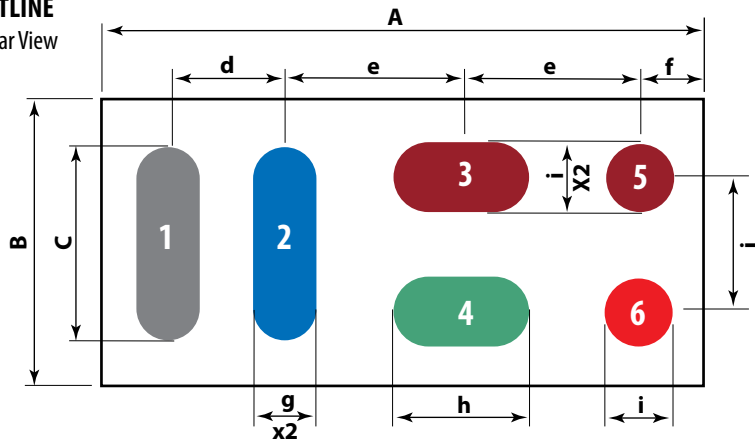
DIE MARKINGS



Part Number	Laser Markings		
	Part # Marking Line 1	Lot_Date Code Marking line 2	Lot_Date Code Marking Line 3
EPC8002	8002	YYYY	ZZZZ

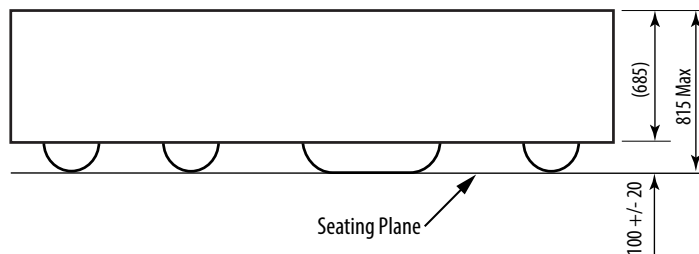
DIE OUTLINE

Solder Bar View



Dim	Micrometers		
	Min	Nominal	Max
A	2020	2050	2080
B	820	850	880
C	555	580	605
d	400	400	400
e	600	600	600
f	200	225	250
g	175	200	225
h	425	450	475
i	175	200	225
j	400	400	400

Side View



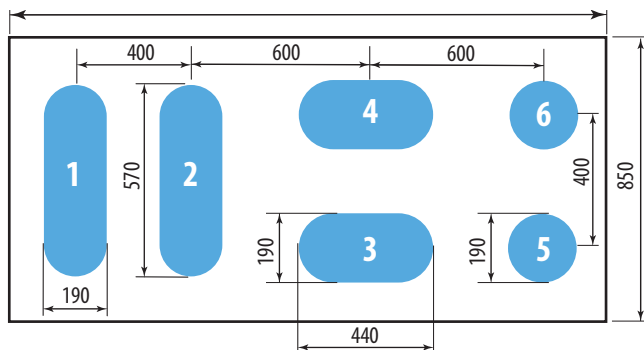
Pad no. 1 is Gate

Pad no. 2 is Source Return for Gate Driver

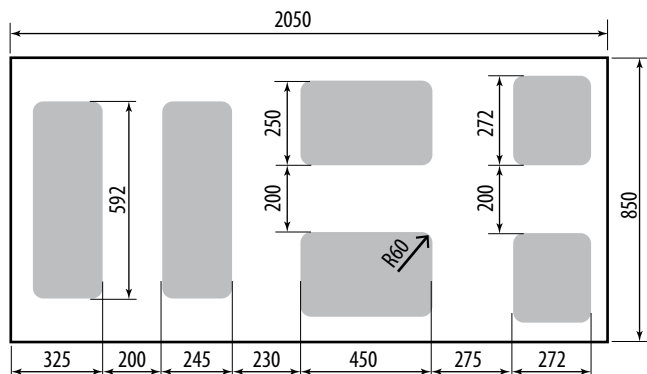
Pad no. 3 and 5 are Source

Pad no. 4 is Drain

Pad no. 6 is Substrate

RECOMMENDED LAND PATTERN(measurements in μm)

The land pattern is solder mask defined.

Solder mask opening is $5\ \mu\text{m}$ smaller per side than bump.**RECOMMENDED STENCIL DRAWING**(measurements in μm)Recommended stencil should be 4 mil (100 μm) thick, must be laser cut, openings per drawing.

Intended for use with SAC305 Type 3 solder, reference 88.5% metals content.

Additional assembly resources available at:

<http://epc-co.com/epc/DesignSupport/AssemblyBasics.aspx>

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Information subject to change without notice.

Revised Oct, 2018